Low Bias Current, 1.8V to 5V Single-Supply, Rail-to-Rail Operational Amplifier

The LMV301 CMOS operational amplifier can operate over a power supply range from 1.8 V to 5 V and has a quiescent current of less than 200 $\mu A,$ maximum, making it ideal for portable battery–operated applications such as notebook computers, PDA's and medical equipment. Low input bias current and high input impedance make it highly tolerant of high source–impedance signal–sources such as photodiodes and pH probes. In addition, the LMV301's excellent rail–to–rail performance will enhance the signal–to–noise performance of any application together with an output stage capable of easily driving a 600 Ω resistive load and up to 1000 pF capacitive load.

Features

- Single Supply Operation (or $\pm V_S/2$)
- V_S from 1.8 V to 5 V
- Low Quiescent Current: 185 μ A, Max with $V_S = 1.8 \text{ V}$
- Rail-to-Rail Output Swing
- Low Bias Current: 35 pA, max
- No Output Phase–Reversal when the Inputs are Overdriven
- These are Pb-Free Devices

Typical Applications

- Portable Battery-Powered Instruments
- Notebook Computers and PDAs
- Cell Phones and Mobile Communication
- Digital Cameras
- Photodiode Amplifiers
- Transducer Amplifiers
- Medical Instrumentation
- Consumer Products



ON Semiconductor®

www.onsemi.com





SC70-5 SQ SUFFIX CASE 419A STYLES 2, 3





TSOP-5 CASE 483



M = Date Code

A = Assembly Location

Y = Year

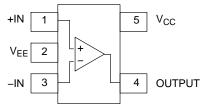
W = Work Week

■ = Pb–Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN CONNECTION



STYLE 3 PINOUT

ORDERING INFORMATION

See detailed ordering and shipping information in the dimensions section on page 11 of this data sheet.

MAXIMUM RATINGS

Symbol	Rating	Value	Unit
V _S	Power Supply (Operating Voltage Range V _S = 1.8 V to 5.0 V)	5.5	V
V_{IDR}	Input Differential Voltage	±Supply Voltage	V
V _{ICR}	Input Common Mode Voltage Range	-0.5 to (V+) + 0.5	V
	Maximum Input Current	10	mA
t _{So}	Output Short Circuit (Note 1)	Continuous	
T_J	Maximum Junction Temperature (Operating Range -40°C to 85°C)	150	°C
J_A	Thermal Resistance (5–Pin SC70–5)	280	°C/W
T _{stg}	Storage Temperature	-65 to 150	°C
	Mounting Temperature (Infrared or Convection (30 sec))	260	
V _{ESD}	ESD Tolerance Machine Model Human Body Model	100 1500	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality

should not be assumed, damage may occur and reliability may be affected.

1. Continuous short–circuit to ground operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of 45 mA over long term may adversely affect reliability. Also, shorting output to V+ will adversely affect reliability; likewise shorting output to V- will adversely affect reliability.

1.8 V DC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for T_A = 25°C, V_{CC} = 1.8 V, R_L = 1 M Ω , V_{EE} = 0 V, V_O = $V_{CC}/2$)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Input Offset Voltage	V _{IO}	$T_A = -40^{\circ}C$ to $+85^{\circ}C$		1.7	9	mV
Input Offset Voltage Average Drift	T_CV_{IO}	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		5		μV/°C
Input Bias Current (Note 2)	I _B			3	35	рА
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$			50	1
Common Mode Rejection Ratio	CMRR	$0 \text{ V} \leq \text{V}_{\text{CM}} \leq 0.9 \text{ V}$	50	63		dB
Power Supply Rejection Ratio	PSRR	$1.8 \text{ V} \le \text{V}_{CC} \le 5 \text{ V}, \\ \text{V}_{O} = 1 \text{ V}, \text{V}_{CM} = 1 \text{ V}$	62	100		dB
Input Common–Mode Voltage Range	V _{СМ}	For CMRR ≥ 50 dB	0 to 0.9	-0.2 to 0.9		V
Large Signal Voltage Gain (Note 2)	A _V	$R_L = 600\Omega$	83	100		dB
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$	80			
		$R_L = 2 k\Omega$	83	100		1
	Ī	$T_A = -40^{\circ}C$ to $+85^{\circ}C$	80			
Output Swing	V _{OH}	$R_L = 600 \Omega \text{ to } 0.9 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	1.65 1.63			V
	V _{OL}	$R_L = 600 \Omega \text{ to } 0.9 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$		75	100 120	mV
	V _{OH}	$R_L = 2 \text{ k}\Omega \text{ to } 0.9 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	1.5 1.4	1.76		V
	V _{OL}	$R_L = 2 \text{ k}\Omega \text{ to } 0.9 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$		25	35 40	mV
Output Short Circuit Current (Note 2)	Io	Sourcing = $V_O = 0 V$ Sinking = $V_O = 1.8 V$	10 20	60 160		mA
Supply Current	I _{CC}	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			185	μΑ

1.8 V AC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for $T_A = 25^{\circ}C$, $V_{CC} = 1.8$ V, $R_L = 1$ M Ω , $V_{EE} = 0$ V, $V_O = V_{CC}/2$)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Slew Rate	S _R			1		V/μs
Gain Bandwidth Product	GBWP	C _L = 200 pF		1		MHz
Phase Margin	Θ_{m}			60		٥
Gain Margin	G _m			10		dB
Input-Referred Voltage Noise	e _n	f = 50 kHz		50		nV/√ Hz
Total Harmonic Distortion	THD	$A_V = +1, V - 1 V_{PP},$ $R_L = 10 \text{ kW, f} = 1 \text{ kHz}$		0.01		%

^{2.} Guaranteed by design and/or characterization.

2.7 V DC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for T_A = 25°C, V_{CC} = 2.7 V, R_L = 1 $M\Omega$, V_{EE} = 0 V, V_O = $V_{CC}/2$)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Input Offset Voltage	V _{IO}	$T_A = -40^{\circ}C$ to $+85^{\circ}C$		1.7	9	mV
Input Offset Voltage Average Drift	T_CV_{IO}	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		5		μV/°C
Input Bias Current (Note 2)	I _B			3	35	pА
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$			50	1
Common Mode Rejection Ratio	CMRR	$0 \text{ V} \leq \text{V}_{\text{CM}} \leq 1.35 \text{ V}$	50	63		dB
Power Supply Rejection Ratio	PSRR	$1.8 \text{ V} \le \text{V}_{CC} \le 5 \text{ V},$ $\text{V}_{O} = 1 \text{ V}, \text{V}_{CM} = 1 \text{ V}$	62	100		dB
Input Common–Mode Voltage Range	V _{CM}	For CMRR ≥ 50 dB	0 to 1.35	-0.2 to1.35		V
Large Signal Voltage Gain (Note 2)	A _V	$R_L = 600 \Omega$	83	100		dB
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$	80			
		$R_L = 2 k\Omega$	83	100		
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$	80			
Output Swing	V _{OH}	$R_L = 600 \Omega \text{ to } 1.35 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	2.55 2.53	2.62		V
	V _{OL}	$R_L = 600 \Omega \text{ to } 1.35 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$		78	100 280	mV
	V _{OH}	$R_L = 2 \text{ k}\Omega \text{ to } 1.35 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	2.65 2.64	2.675		V
	V _{OL}	$R_L = 2 \text{ k}\Omega \text{ to } 1.35 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$		75	100 110	mV
Output Short Circuit Current (Note 2)	Io	Sourcing = $V_O = 0 V$ Sinking = $V_O = 2.7 V$	10 20	60 160		mA
Supply Current	I _{CC}	$T_A = -40^{\circ}C$ to $+85^{\circ}C$			185	μΑ

2.7 V AC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for $T_A = 25^{\circ}C$, $V_{CC} = 2.7$ V, $R_L = 1$ M Ω , $V_{EE} = 0$ V, $V_O = V_{CC}/2$)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Slew Rate	S _R			1		V/μs
Gain Bandwidth Product	GBWP	C _L = 200 pF		1		MHz
Phase Margin	Θ_{m}			60		0
Gain Margin	G _m			10		dB
Input-Referred Voltage Noise	e _n	f = 50 kHz		50		nV/√Hz
Total Harmonic Distortion	THD	$A_V = +1, V - 1 V_{PP},$ $R_L = 10 \text{ kW}, f = 1 \text{ kHz}$		0.01		%

^{2.} Guaranteed by design and/or characterization.

5.0 V DC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for $T_A = 25$ °C, $V_{CC} = 5.0$ V, $R_L = 1$ M Ω , $V_{EE} = 0$ V, $V_O = V_{CC}/2$)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Input Offset Voltage	V _{IO}	$T_A = -40^{\circ}C$ to $+85^{\circ}C$		1.7	9	mV
Input Offset Voltage Average Drift	T_CV_{IO}	$T_A = -40^{\circ}C$ to $+85^{\circ}C$		5		μV/°C
Input Bias Current (Note 2)	I _B			3	35	рА
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$			50	1
Common Mode Rejection Ratio	CMRR	$0 \text{ V} \leq \text{V}_{\text{CM}} \leq 4 \text{ V}$	50	63		dB
Power Supply Rejection Ratio	PSRR	$1.8 \text{ V} \le \text{V}_{CC} \le 5 \text{ V},$ $\text{V}_{O} = 1 \text{ V}, \text{V}_{CM} = 1 \text{ V}$	62	100		dB
Input Common–Mode Voltage Range	V _{CM}	For CMRR ≥ 50 dB	0 to 4	-0.2 to 4.2		V
Large Signal Voltage Gain (Note 2)	A _V	$R_L = 600 \Omega$	83	100		dB
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$	80			1
		$R_L = 2 k\Omega$	83	100		
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$	80			
Output Swing	V _{OH}	$R_L = 600 \Omega \text{ to } 2.5 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	4.850 4.840			V
	V _{OL}	$R_L = 600 \Omega \text{ to } 2.5 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$			150 160	mV
	V _{OH}	$R_L = 2 \text{ k}\Omega \text{ to } 2.5 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	4.935 4.900			V
	V _{OL}	$R_L = 2 \text{ k}\Omega \text{ to } 2.5 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$			65 75	mV
Output Short Circuit Current (Note 2)	I _O	Sourcing = $V_O = 0 V$ Sinking = $V_O = 5 V$	10 10	60 160		mA
Supply Current	I _{CC}	$T_A = -40^{\circ}C$ to $+85^{\circ}C$			200	μΑ

5.0 V AC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for $T_A = 25^{\circ}C$, $V_{CC} = 5.0$ V, $R_L = 1$ M Ω , $V_{EE} = 0$ V, $V_O = V_{CC}/2$)

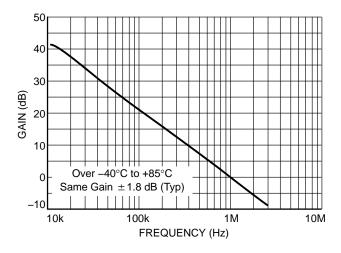
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Slew Rate	S _R			1		V/μs
Gain Bandwidth Product	GBWP	C _L = 200 pF		1		MHz
Phase Margin	Θ_{m}			60		٥
Gain Margin	G _m			10		dB
Input-Referred Voltage Noise	e _n	f = 50 kHz		50		nV/√Hz
Total Harmonic Distortion	THD	$A_V = +1, V - 1 V_{PP},$ $R_L = 10 \text{ kW, f} = 1 \text{ kHz}$		0.01		%

^{2.} Guaranteed by design and/or characterization.

TYPICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ and } V_S = 5 \text{ V unless otherwise specified})$

100



90 80 70 80 70 90 40 10k 100k 1M 10M FREQUENCY (Hz)

Figure 1. Open Loop Frequency Response $(R_L = 2 \text{ k}\Omega, T_A = 25^{\circ}\text{C}, V_S = 5 \text{ V})$

100

90

80 70

60

50

40

30 20

10

80

70

60

50

40

30

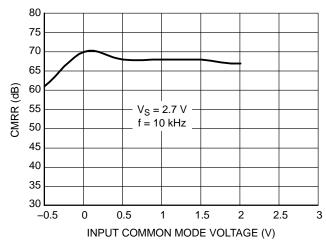
CMRR (dB)

10

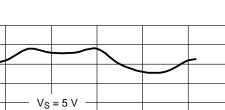
CMRR (dB)

100 1k 10k 100k

Figure 2. Open Loop Phase Margin ($R_L = 2 k\Omega$, $T_A = 25$ °C)



 $\begin{aligned} & \text{FREQUENCY (Hz)} \\ \textbf{Figure 3. CMRR vs. Frequency} \\ & \left(\textbf{R}_{L} = 5 \text{ k} \Omega, \text{ V}_{S} = 5 \text{ V} \right) \end{aligned}$



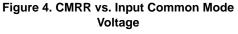
f = 10 kHz

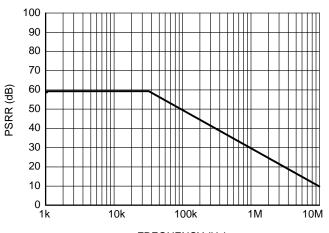
INPUT COMMON MODE VOLTAGE (V)

Figure 5. CMRR vs. Input Common Mode

Voltage

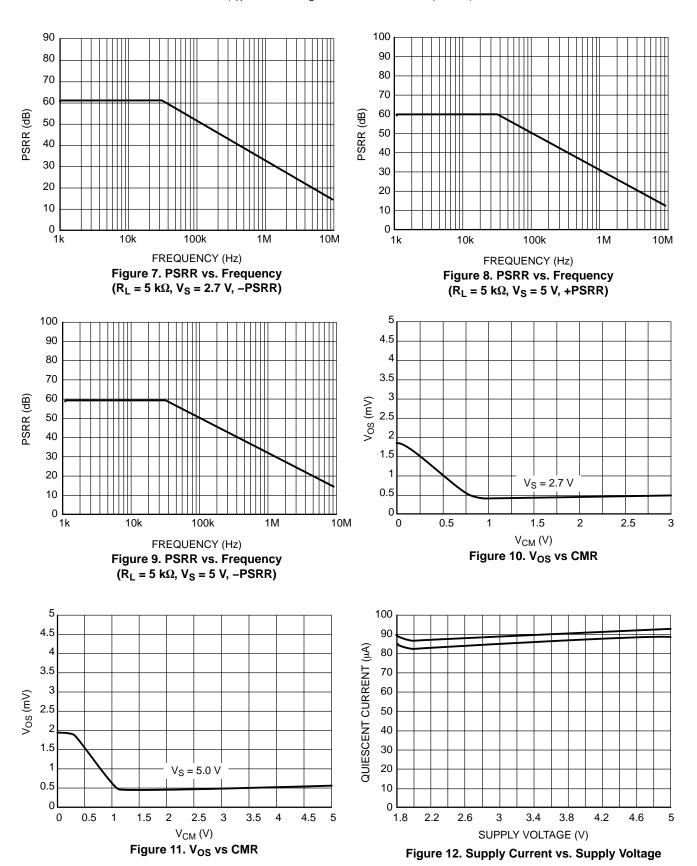
2





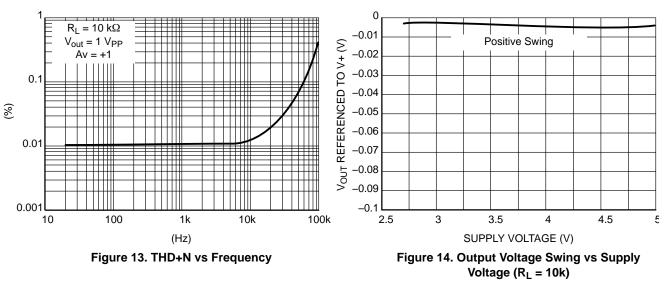
TYPICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ and } V_S = 5 \text{ V unless otherwise specified})$



TYPICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ and } V_S = 5 \text{ V unless otherwise specified})$



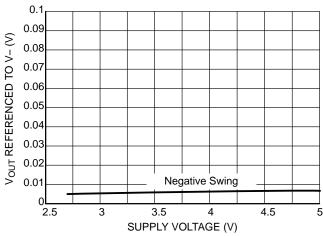


Figure 15. Output Voltage Swing vs Supply Voltage (R_L = 10k)

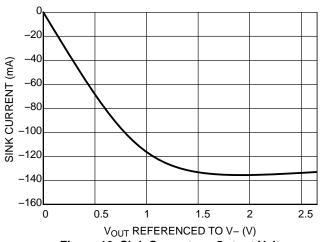


Figure 16. Sink Current vs. Output Voltage $V_S = 2.7 \text{ V}$

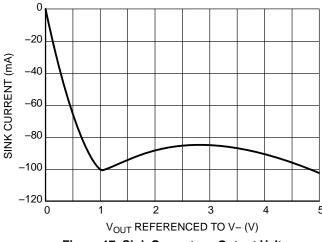


Figure 17. Sink Current vs. Output Voltage $V_S = 5.0 \text{ V}$

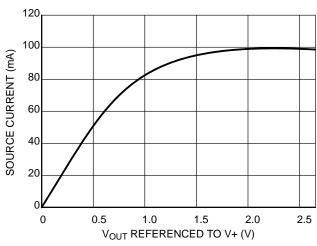


Figure 18. Source Current vs. Output Voltage $V_S = 2.7 \text{ V}$

TYPICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ and } V_S = 5 \text{ V unless otherwise specified})$

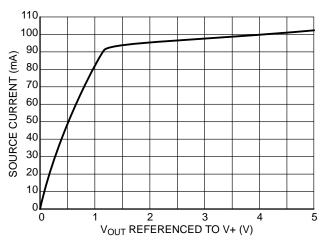


Figure 19. Source Current vs. Output Voltage $V_S = 5.0 \text{ V}$

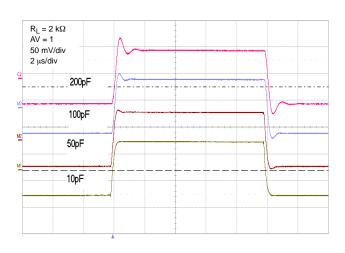


Figure 20. Settling Time vs. Capacitive Load

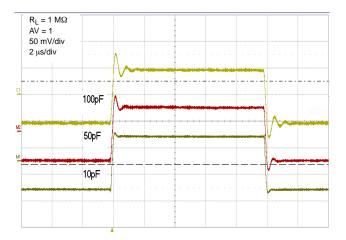


Figure 21. Settling Time vs. Capacitive Load

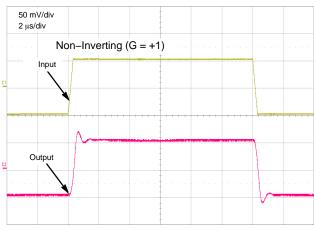


Figure 22. Step Response – Small Signal

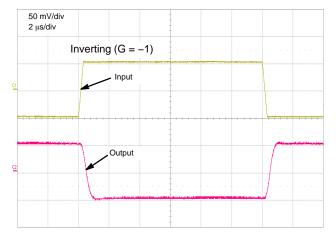


Figure 23. Step Response - Small Signal

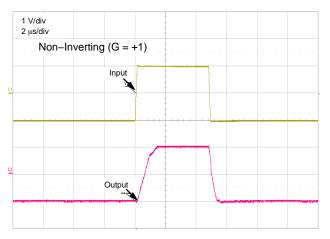


Figure 24. Step Response - Large Signal

TYPICAL CHARACTERISTICS

(T_A = 25° C and V_S = 5 V unless otherwise specified)

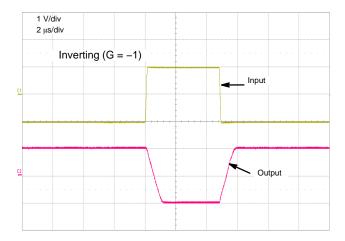


Figure 25. Step Response – Large Signal

APPLICATIONS

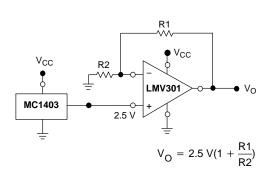


Figure 26. Voltage Reference

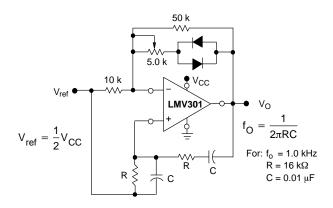


Figure 27. Wien Bridge Oscillator

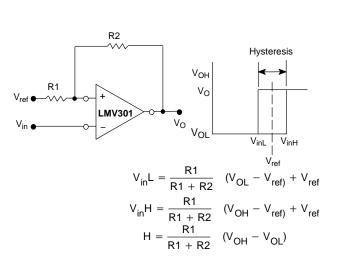
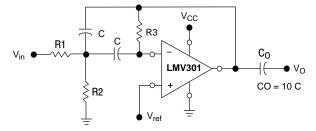


Figure 28. Comparator with Hysteresis



Given: f_0 = center frequency $A(f_0)$ = gain at center frequency

Choose value
$$f_0$$
, $\frac{C}{Q}$
Then: $R3 = \frac{Q}{\pi f_0 C}$
$$R1 = \frac{R3}{2 A(f_0)}$$

$$R2 = \frac{R1 R3}{4Q^2 R1 - R3}$$

For less than 10% error from operational amplifier, (($Q_O f_O$)/BW) < 0.1 where f_O and BW are expressed in Hz. If source impedance varies, filter may be preceded with voltage follower buffer to stabilize filter parameters.

Figure 29. Multiple Feedback Bandpass Filter

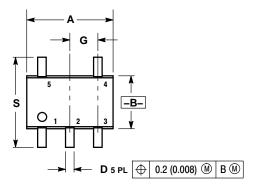
ORDERING INFORMATION

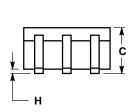
Device	Pinout Style	Marking	Package	Shipping [†]
LMV301SQ3T2G	Style 3	AAD	SC70-5 (Pb-Free)	3000 / Tape & Reel
LMV301SN3T1G	Style 3	ADY	TSOP-5 (Pb-Free)	3000 / Tape & Reel

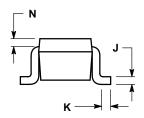
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE L







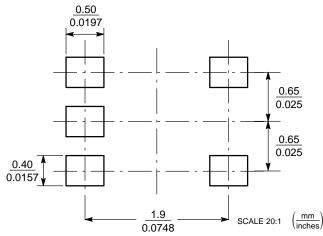
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65	BSC
Н		0.004		0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008	REF	0.20	REF
_ c	0.070	0.097	2.00	2 20

- STYLE 2: PIN 1. ANODE 2. EMITTER 3. BASE 4. COLLECTOR 5. CATHODE

- STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1

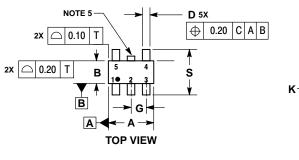
SOLDERING FOOTPRINT*



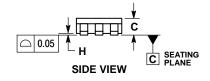
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

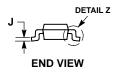
PACKAGE DIMENSIONS

TSOP-5 **CASE 483 ISSUE M**







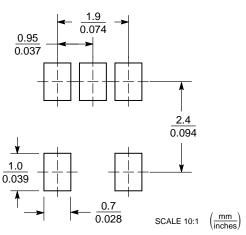


NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- DIMENSIONING AND TOLERANGING FER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD DIMENSIONS A AND 6 DO NOT INCLUDE MICLE
 FLASH, PROTRUSIONS, OR GATE BURRS. MOLD
 FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT
 EXCEED 0.15 PER SIDE. DIMENSION A.
 OPTIONAL CONSTRUCTION: AN ADDITIONAL
 TRIMMED LEAD IS ALLOWED IN THIS LOCATION.
- TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.85	3.15		
В	1.35	1.65		
С	0.90	1.10		
D	0.25	0.50		
G	0.95	BSC		
Н	0.01	0.10		
J	0.10	0.26		
K	0.20	0.60		
М	0 °	10 °		
S	2.50	3.00		

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center

Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative